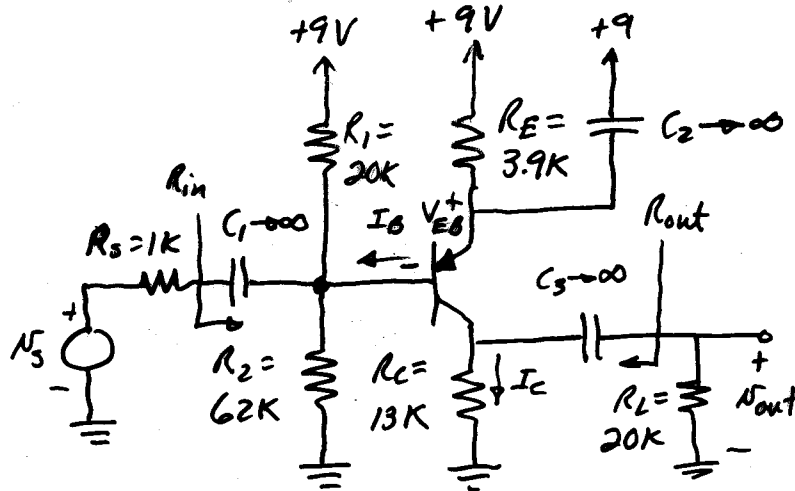
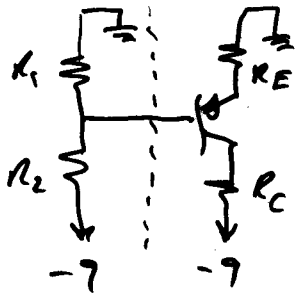


PNP Example

If $\beta_0 = 135$ and $V_A = 100V$, find $\frac{N_{out}}{N_s}$, R_{in} and R_{out} .

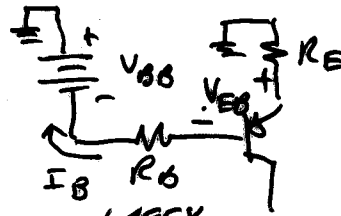


1.) Q point



$$V_{BB} = -9V \frac{R_1}{R_1 + R_2} = \frac{-9(20K)}{82K} = -2.195V$$

$$R_B = R_1 || R_2 = 15.12K$$



$$I_B = \frac{2.195 - 0.7}{R_B + (1 + \beta_0) R_E} = \frac{1.495V}{15.12K + (136 \cdot 3.9K)} = 2.75 \mu A$$

$$I_C = 135 \cdot I_B = 0.37 \mu A \rightarrow I_E = 0.373 \mu A$$

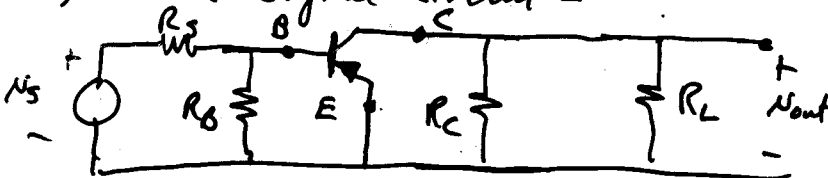
$$V_{EC} = 9 - I_C R_C - I_E R_E = 9 - 4.81 - 1.454 = 2.736V$$

2.) Small-signal model parameters

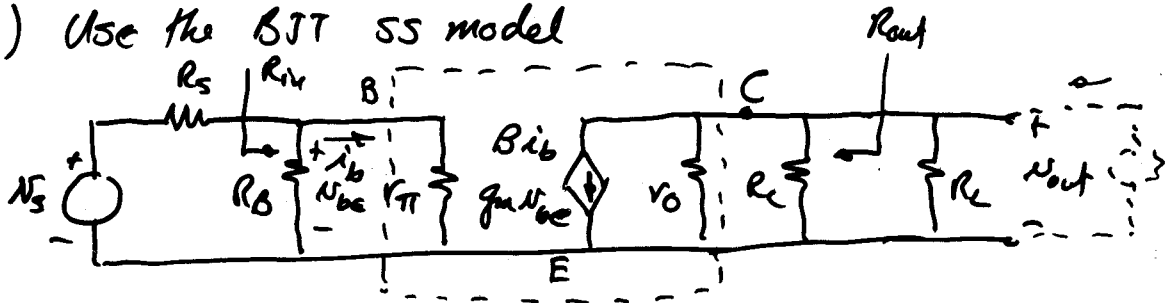
$$g_m = \frac{I_C}{V_T} = \frac{0.37 \mu A}{25 mV} = 14.8 \mu S, \quad r_{\pi} = \frac{\beta_0}{g_m} = \frac{135}{14.8} K = 9.12 K \Omega$$

$$r_o = \frac{V_A + V_{EE}}{I_C} = \frac{100 + 2.736}{0.37 \mu A} = 278 K \Omega$$

3.) Small-signal circuit -



4.) Use the BJT SS model



$$R_{in} = R_b \parallel r_{\pi} = \underline{5.659k\Omega} \quad R_{out} = r_o \parallel R_c = \underline{12.42k\Omega}$$

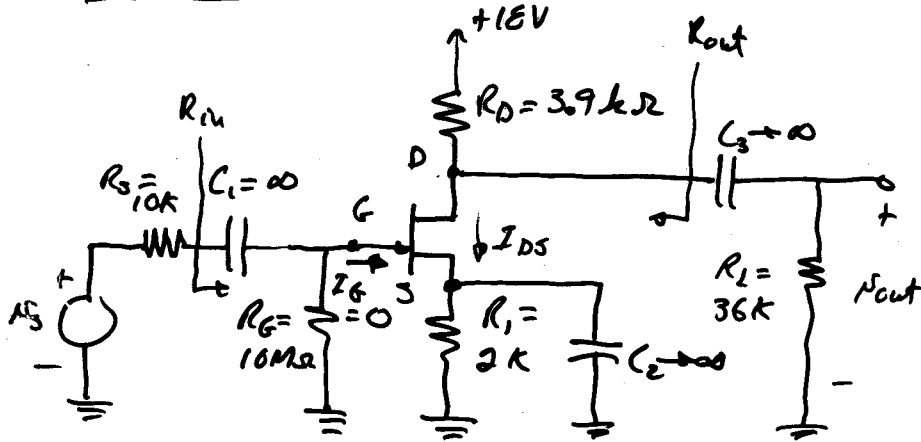
$$R_{out} = \frac{N_{test}}{\lambda_{test}}$$

$$\frac{N_{out}}{N_s} = \left(\frac{N_{out}}{N_{be}}\right) \left(\frac{N_{be}}{N_s}\right) = \left[-g_m(r_o \parallel R_c \parallel R_L)\right] \left[\frac{R_b \parallel r_{\pi}}{R_s + R_b \parallel r_{\pi}}\right]$$

$$\left[-14.8 \times (27k \parallel 13k \parallel 20k)\right] \left[\frac{R_{in}}{R_s + R_{in}}\right] = \underline{\underline{-96.44 V/V}}$$

\uparrow
 $\frac{5.659k}{6.659k}$

JFET Example



If $I_{DSS} = 5mA$,
 $V_p = -5V$ and
 $\frac{1}{\lambda} = 50V$ and
 $I_D = 1.25mA$ and
 $V_{DS} = 10.6V$ and
 if the JFET is in saturation region, then find R_{in} , R_{out} &

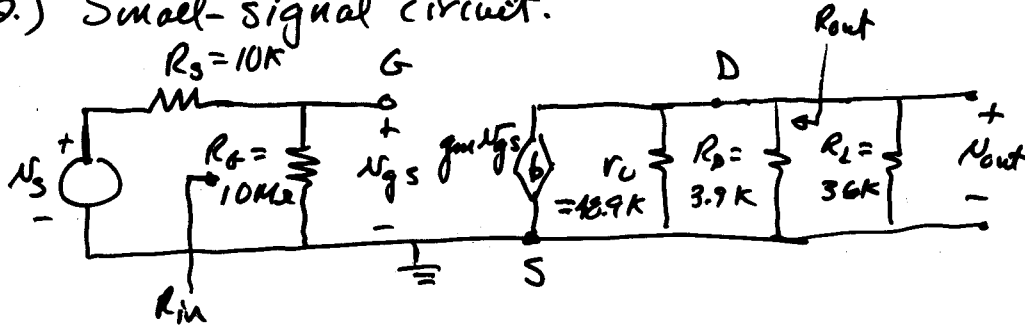
$$1.) \quad g_m = \frac{2}{|V_p|} \sqrt{I_{DSS} I_D (1 + \lambda V_{DS})}$$

$$= \frac{2}{5} \sqrt{(5mA)(1.25mA) \left(1 + \frac{10.6}{50}\right)} = 1.1mS$$

$$r_o = \frac{1}{\lambda} + \frac{V_{DS}}{I_{DS}} = \frac{50 + 10.6}{1.25mA} = 48.48k\Omega$$

$$\frac{N_{out}}{N_{in}}$$

2.) Small-signal circuit.



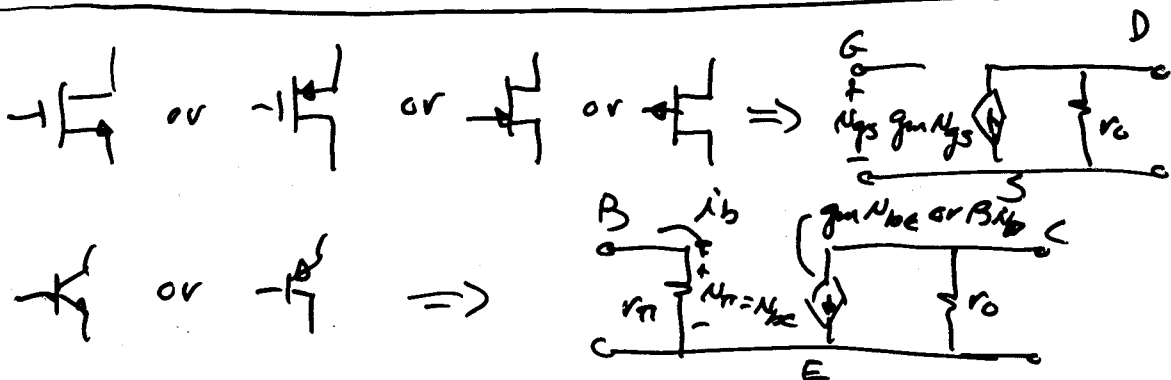
$$R_{in} = 10M\Omega, R_{out} = r_o \parallel R_D = 3.61k\Omega$$

$$\frac{v_{out}}{v_s} = \left(\frac{v_{out}}{v_{gs}} \right) \left(\frac{v_{gs}}{v_s} \right) = \left(-g_m \times r_o \parallel R_D \parallel R_L \right) \left(\frac{R_G}{R_s + R_G} \right)$$

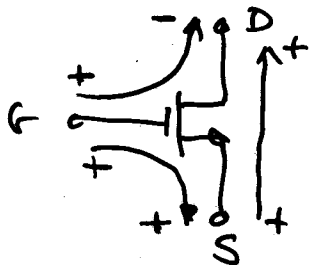
$$= -1.1 (3.281) \left(\frac{10}{10.01} \right) = -3.605 \frac{V}{V}$$

Study Table 13.5 in text.

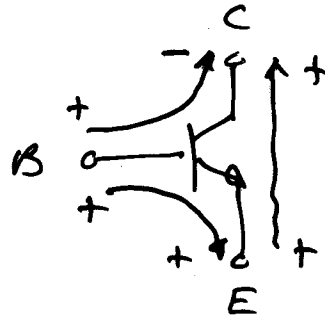
	CE	CS
$\frac{v_{out}}{v_s}$	-	-
R_{in}	-	-
R_{out}	-	-



Signal Flow in transistors

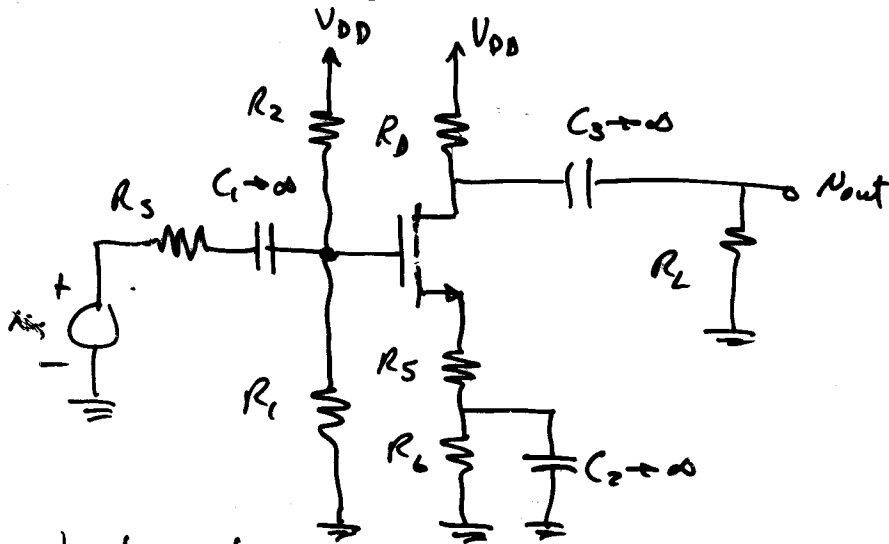


The gate is NEVER an output.
The drain is NEVER an input.



The base is NEVER an output.
The collector is NEVER an input.

Common Nothing



Looking ahead -

